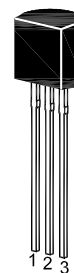


# ST 8550

## PNP Silicon Epitaxial Planar Transistor

for switching and amplifier applications. Especially suitable for AF-driver stages and low power output stages.

The transistor is subdivided into four groups, B, C, D and E, according to its DC current gain. As complementary type the NPN transistor ST 8050 is recommended.



1. Emitter 2. Base 3. Collector  
TO-92 Plastic Package

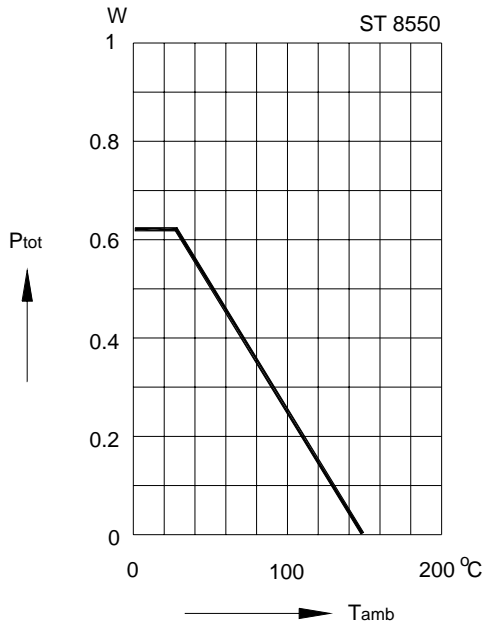
### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	40	V
Collector Emitter Voltage	$-V_{CEO}$	25	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current	$-I_C$	800	mA
Peak Collector Current	$-I_{CM}$	1	A
Base Current	$-I_B$	100	mA
Power Dissipation	$P_{tot}$	625	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

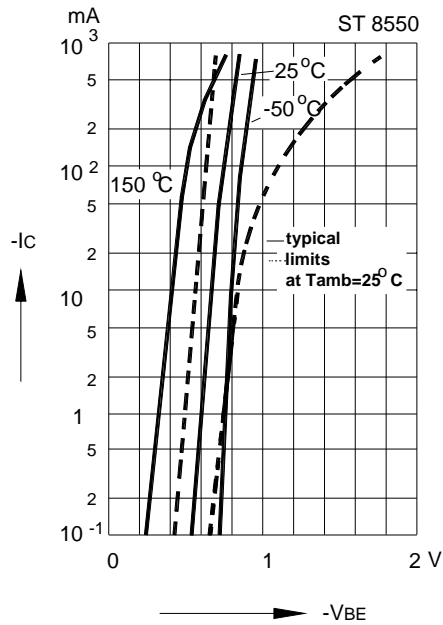
### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $-V_{CE} = 1\text{ V}$ , $-I_C = 100\text{ mA}$  at $-V_{CE} = 1\text{ V}$ , $-I_C = 350\text{ mA}$	Current Gain Group B	$h_{FE}$	70	-	120	-
	C	$h_{FE}$	120	-	200	-
	D	$h_{FE}$	160	-	300	-
	E	$h_{FE}$	300	-	380	-
		$h_{FE}$	60	-	-	-
Collector Base Cutoff Current at $-V_{CB} = 35\text{ V}$	$-I_{CBO}$	-	-	100	nA	
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	40	-	-	V	
Collector Emitter Breakdown Voltage at $-I_C = 2\text{ mA}$	$-V_{(BR)CEO}$	25	-	-	V	
Emitter Base Breakdown Voltage at $-I_E = 100\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	6	-	-	V	
Collector Emitter Saturation Voltage at $-I_C = 500\text{ mA}$ , $-I_B = 50\text{ mA}$	$-V_{CE(sat)}$	-	-	0.5	V	
Base Emitter Saturation Voltage at $-I_C = 500\text{ mA}$ , $-I_B = 50\text{ mA}$	$-V_{BE(sat)}$	-	-	1.2	V	
Gain Bandwidth Product at $-V_{CE} = 5\text{ V}$ , $-I_C = 10\text{ mA}$ , $f = 50\text{ MHz}$	$f_T$	-	100	-	MHz	
Collector Base Capacitance at $-V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$	$C_{cbo}$	-	12	-	pF	

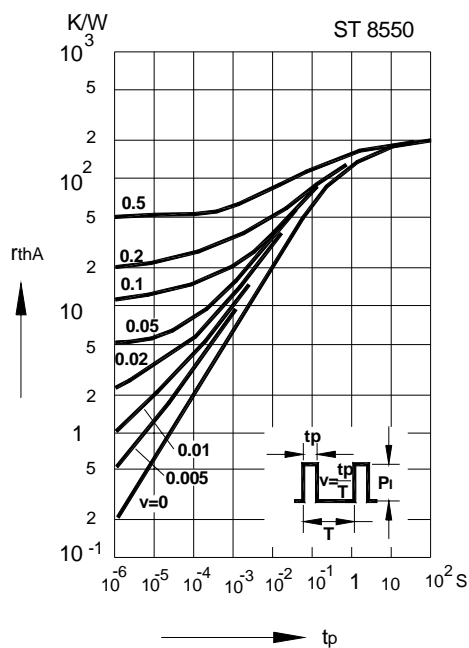
**Admissible power dissipation versus ambient temperature**  
Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case



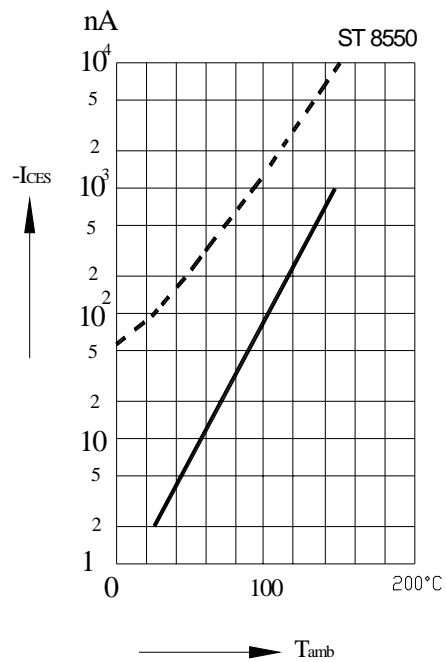
**Collector current versus base emitter voltage**



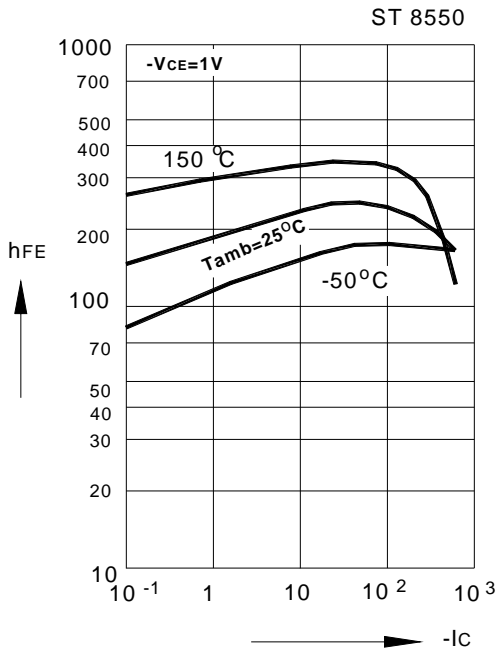
**Pulse thermal resistance versus pulse duration**  
Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case



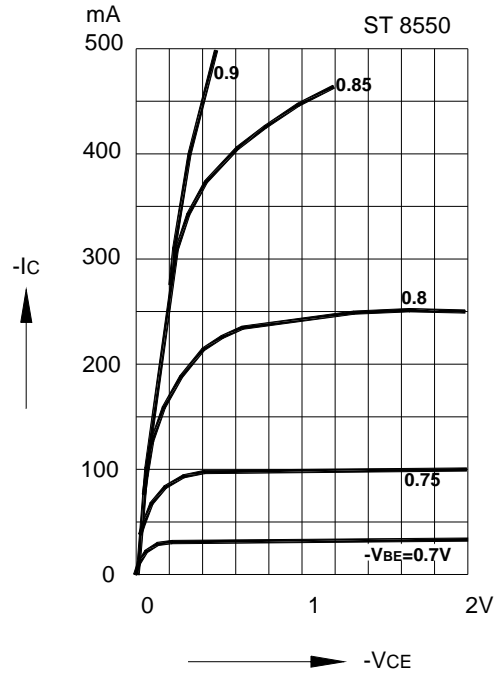
**Collector cutoff current versus ambient temperature**



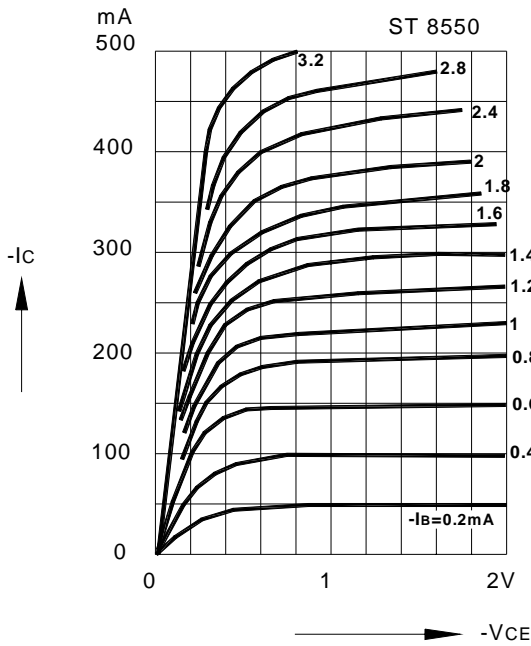
**DC current gain versus collector current**



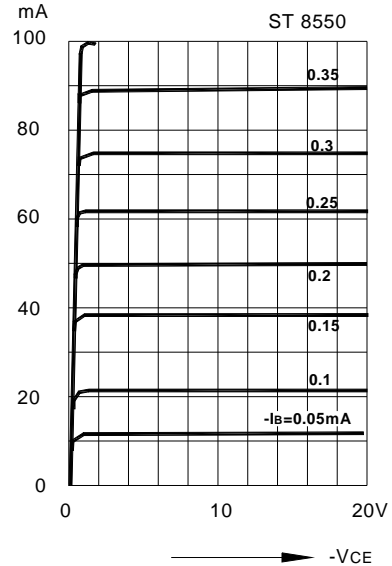
**Common emitter collector characteristics**



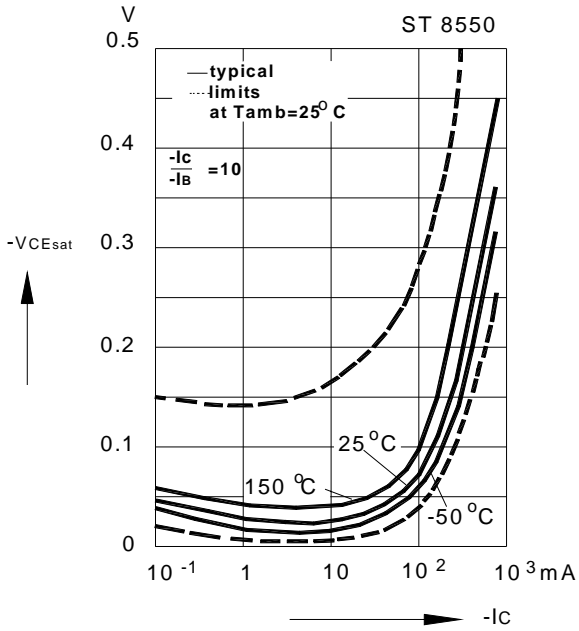
**Common emitter collector characteristics**



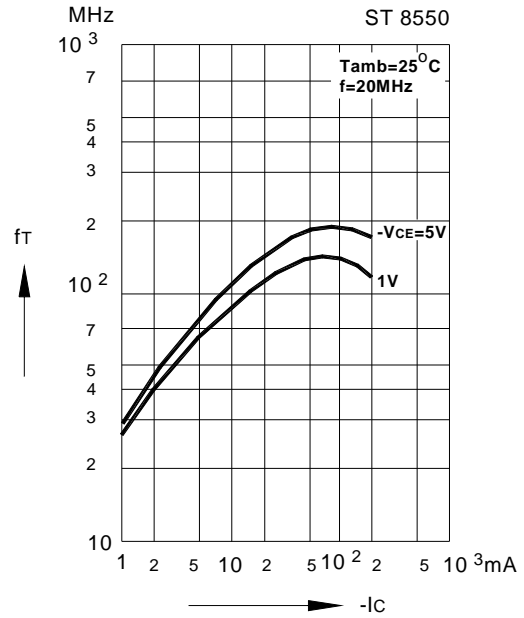
**Common emitter collector characteristics**



**Collector saturation voltage versus collector current**



**Gain bandwidth product versus collector current**



**Base saturation voltage versus collector current**

